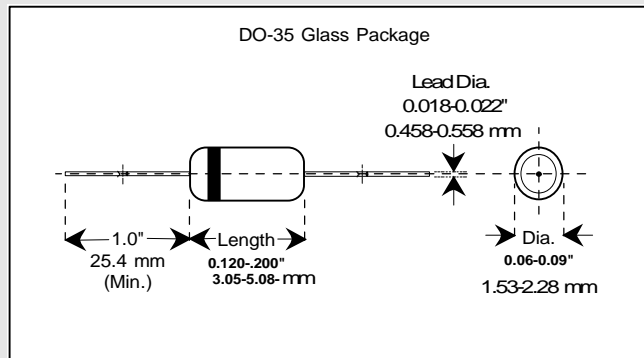


Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings		Symbol	Value	Unit
Peak Inverse Voltage		PIV	85 (Min).	Volts
Average Rectified Current		I _{avg}	200	mAmps
Continuous Forward Current		I _{Fdc}	200	mAmps
Peak Surge Current (t _{peak} = 1 sec.)		I _{peak}	1.0	Amp
BKC Power Dissipation T _L = 50 °C, L = 3/8" from body		P _{tot}	500	mWatts
Operating Temperature Range		T _{Op}	-65 to +200	° C
Storage Temperature Range		T _{St}	-65 to +200	° C
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

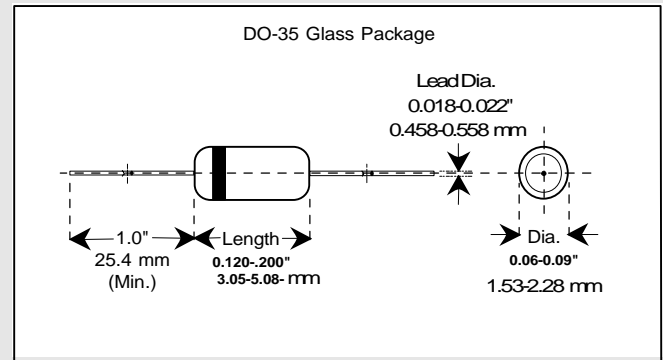
Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

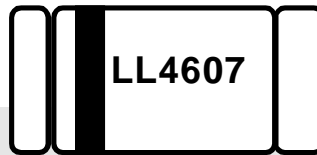
- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings		Symbol	Value	Unit
Peak Inverse Voltage		PIV	85 (Min).	Volts
Average Rectified Current		Iavg	200	mAmps
Continuous Forward Current		I _{Fdc}	500	mAmps
Peak Surge Current (t _{peak} = 1 sec.)		I _{peak}	1.0	Amp
BKC Power Dissipation T _L =50 °C, L = 3/8" from body		P _{tot}	500	mWatts
Operating Temperature Range		T _{Op}	-65 to +150	° C
Storage Temperature Range		T _{St}	-65 to +150	° C
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 μA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	μA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with $I_F = 10$ mA, $V_R = 6$ V, $R_L = 100$ Ohms. * UNLESS OTHERWISE SPECIFIED

Silicon Switching Diode



LL4607

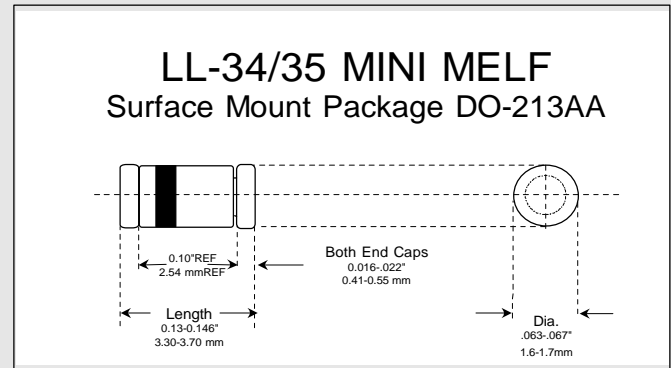
L-35 Glass Package

Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability



Maximum Ratings		Symbol	Value	Unit
Peak Inverse Voltage		PIV	85 (Min).	Volts
Average Rectified Current		I _{avg}	200	mAmps
Continuous Forward Current		I _{Fdc}	200	mAmps
Peak Surge Current (t _{peak} = 1 sec.)		I _{peak}	1.0	Amp
BKC Power Dissipation		P _{tot}	500	mWatts
Operating Temperature Range		T _{Op}	-65 to +200	° C
Storage Temperature Range		T _{St}	-65 to +200	° C
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 µA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	µA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_R = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED



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Silicon Switching Diode

LL4608

LL-35 Glass Package

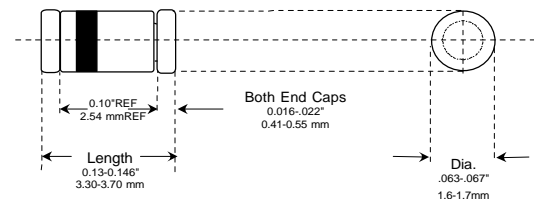
Applications

Used in general purpose applications, where a controlled forward characteristic and fast switching speed are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability

LL-34/35 MINI MELF Surface Mount Package DO-213AA



Maximum Ratings		Symbol	Value	Unit
Peak Inverse Voltage		PIV	85 (Min).	Volts
Average Rectified Current		Iavg	200	mAmps
Continuous Forward Current		I _{Fdc}	500	mAmps
Peak Surge Current (t _{peak} = 1 sec.)		I _{peak}	1.0	Amp
BKC Power Dissipation T _L =50 °C, L = 3/8" from body		P _{tot}	500	mWatts
Operating Temperature Range		T _{Op}	-65 to +150	° C
Storage Temperature Range		T _{St}	-65 to +150	° C
Electrical Characteristics @ 25 °C*	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ I _F = 400 mA	V _F	***	1.10	Volts
Breakdown Voltage @ I _R = 25 µA	PIV	85		Volts
Reverse Leakage Current @ V _R = 50 V	I _R		100	µA
Reverse Recovery time (note 1)	t _{rr}		10	nSecs

Note 1: Per Method 4031-A with I_F = 10 mA, V_r = 6 V, R_L = 100 Ohms. * UNLESS OTHERWISE SPECIFIED



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